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MOSFET - Power, Single N-Channel, DUAL COOL™, DFN8 5x6.15

40 V, 1.0 mΩ, 288 A



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NTMFSC1D0N04HL

Features

- Advanced Dual-Side Cooled Packaging
- Ultra Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_g and Q_{oss} to Minimize Charge Losses
- MSL1 Robust Packaging Design
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- DC-DC Conversion
- Orring FET/Load Switching
- Synchronous Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, Unless otherwise specified)

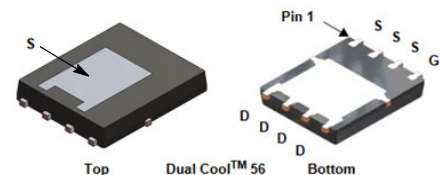
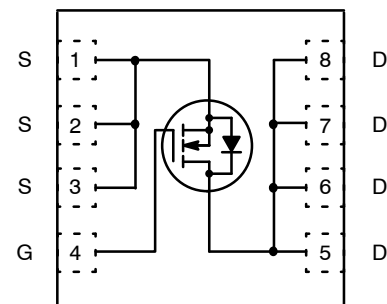
Parameter			Symbol	Value	Unit
Drain-to-Source Breakdown Voltage			$V_{(BR)DSS}$	40	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Note 2)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	288	A
Power Dissipation $R_{\theta JC}$ (Note 2)			P_D	166	W
Continuous Drain Current $R_{\theta JA}$ (Note 1, 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	43	A
Power Dissipation $R_{\theta JA}$ (Note 1, 2)			P_D	3.8	W
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 100\text{ }\mu\text{s}$		I_{DM}	1189	A
Operating Junction and Storage Temperature Range			T_J , T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	177	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{AV} = 45\text{ A}$)			E_{AS}	304	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in² pad size, 1 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

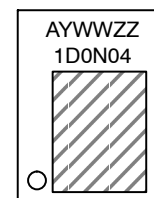
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	1.0 mΩ @ 10 V	288 A
	1.5 mΩ @ 4.5 V	

N-Channel MOSFET



DFN8 5x6.15
CASE 506EG

MARKING DIAGRAM



1D0N04 = Specific Device Code
A = Assembly Plant Code
YWW = Date Code (Year & Week)
ZZ = Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NTMFSC1D0N04HL

THERMAL CHARACTERISTICS

Symbol	Parameter	Max	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State (Note 2)	0.9	°C/W
$R_{\theta JT}$	Junction-to-Top Source – Steady State (Note 2)	1.4	
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	39	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS} / T_J$			25		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)} / T_J$	$I_D = 250\text{ }\mu\text{A}, \text{ref to } 25^\circ\text{C}$		-5.7		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		0.8	1.0	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 40\text{ A}$		1.2	1.5	
Forward Trans-conductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 50\text{ A}$		500		S
Gate-Resistance	R_G	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1	2.6	Ω

CHARGES & CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 20\text{ V}$		5960		pF
Output Capacitance	C_{OSS}			1360		
Reverse Transfer Capacitance	C_{RSS}			59		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}$		93		nC
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}$		43		
Threshold Gate Charge	$Q_{G(TH)}$			8.7		nC
Gate-to-Source Charge	Q_{GS}			15		
Gate-to-Drain Charge	Q_{GD}			13		
Output Charge	Q_{OSS}	$V_{DD} = 20\text{ V}, V_{GS} = 0\text{ V}$		86		nC

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.5\text{ }\Omega$		28		ns
Rise Time	t_r			36		
Turn-Off Delay Time	$t_{d(OFF)}$			44		
Fall Time	t_f			17		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}$	$T_J = 25^\circ\text{C}$		0.78	1.2	V
			$T_J = 150^\circ\text{C}$		0.6		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$			54		ns
Reverse Recovery Charge	Q_{RR}				78		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

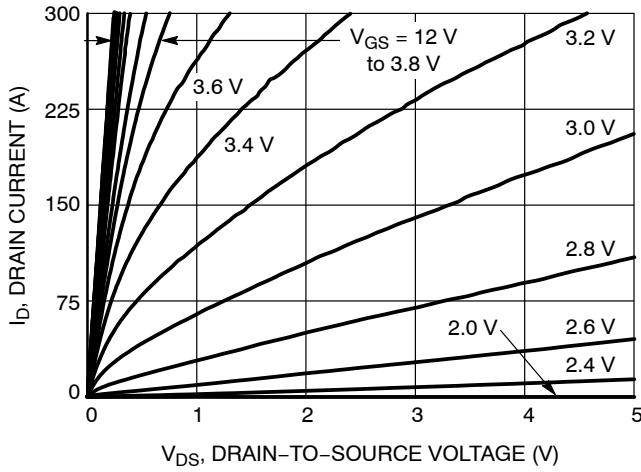


Figure 1. On-Region Characteristics

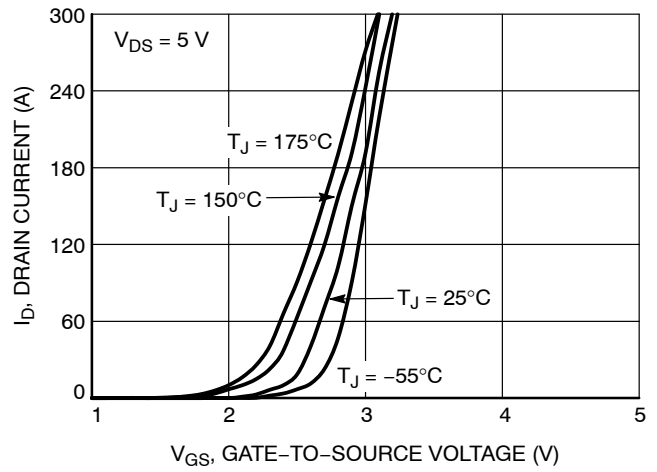


Figure 2. Transfer Characteristics

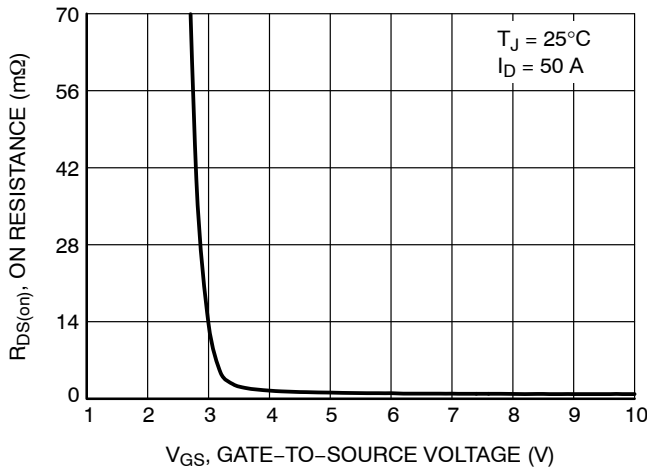


Figure 3. On-Resistance vs. Gate-to-Source Voltage

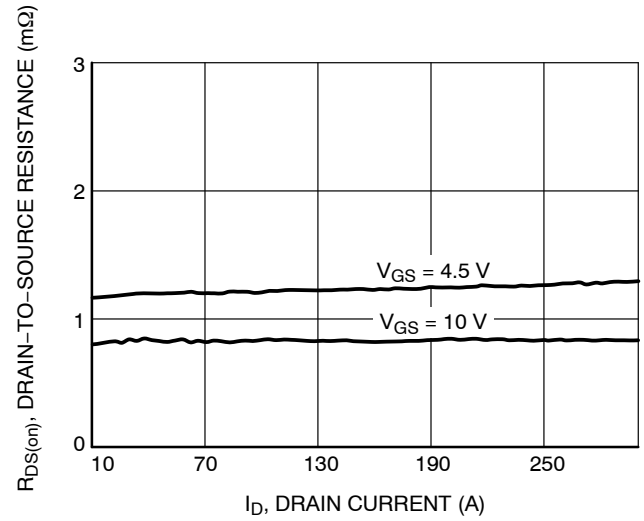


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

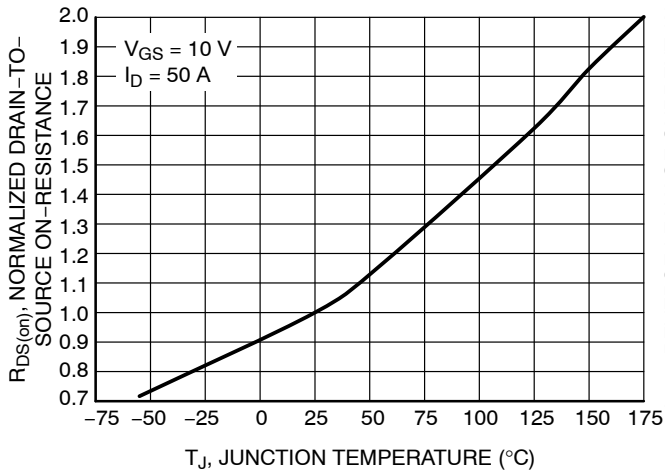


Figure 5. On-Resistance Variation with Temperature

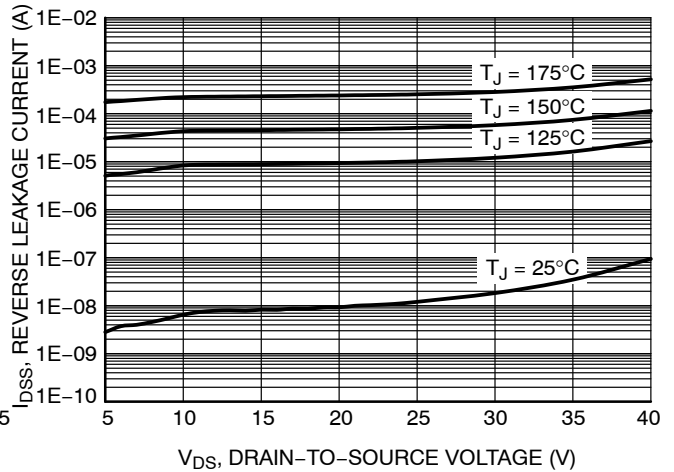


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

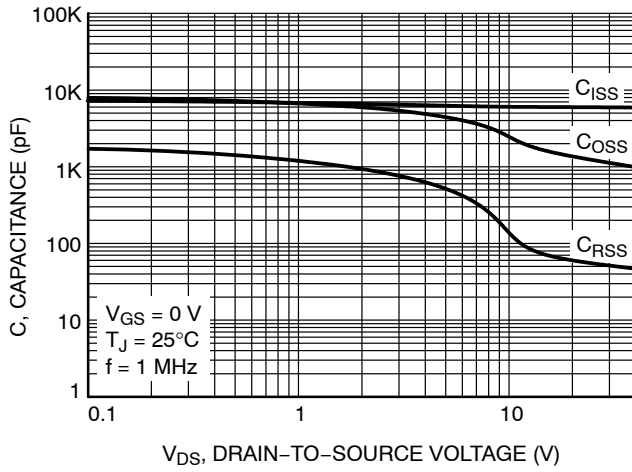


Figure 7. Capacitance Variation

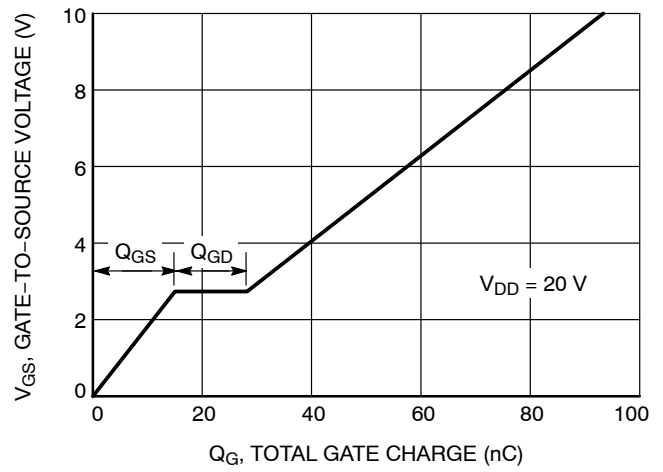


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

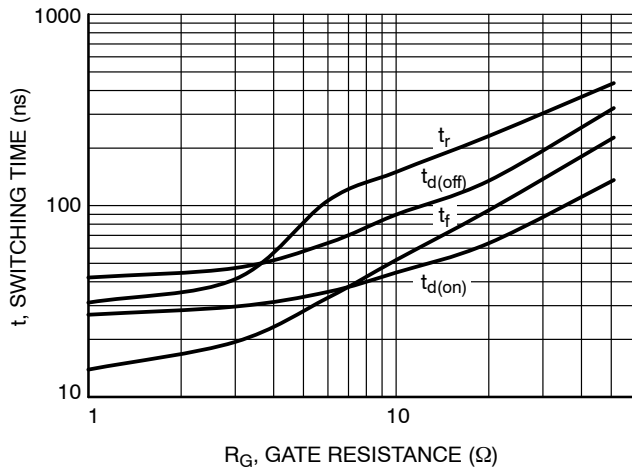


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

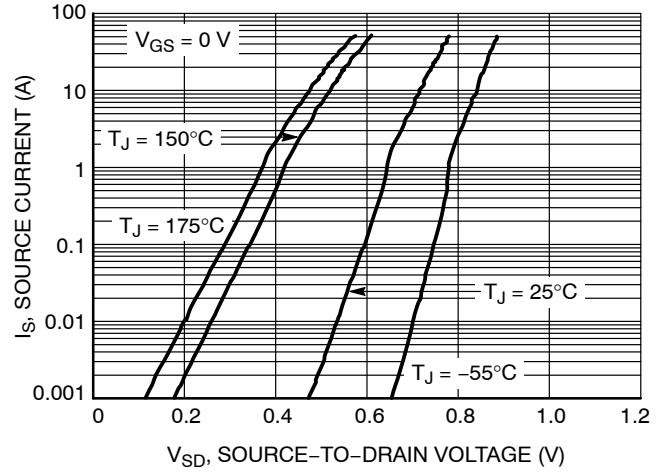


Figure 10. Diode Forward Voltage vs. Current

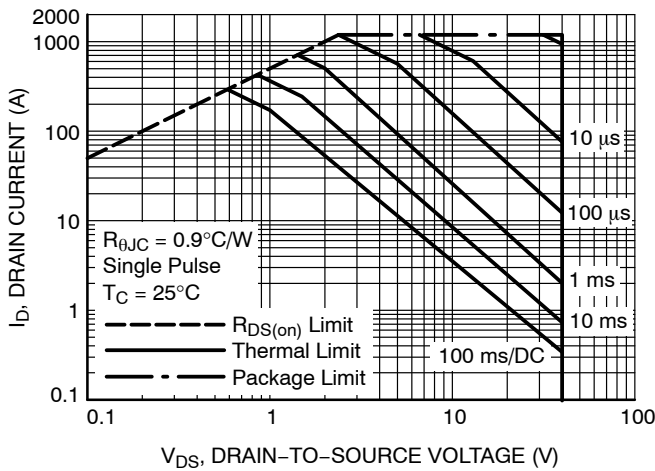


Figure 11. Forward Bias Safe Operating Area

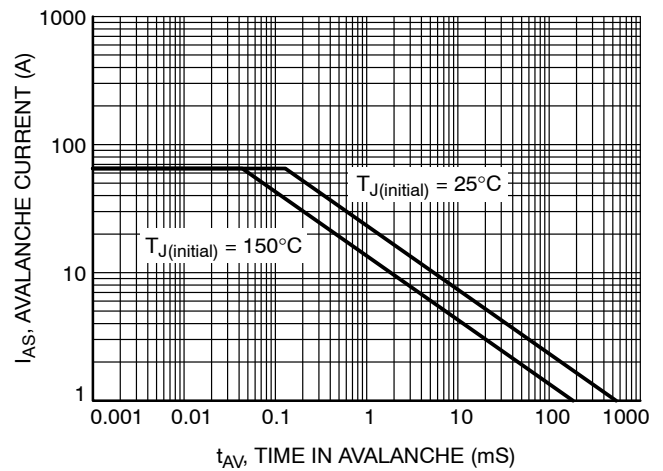


Figure 12. Unclamped Inductive Switching Capability

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TYPICAL CHARACTERISTICS

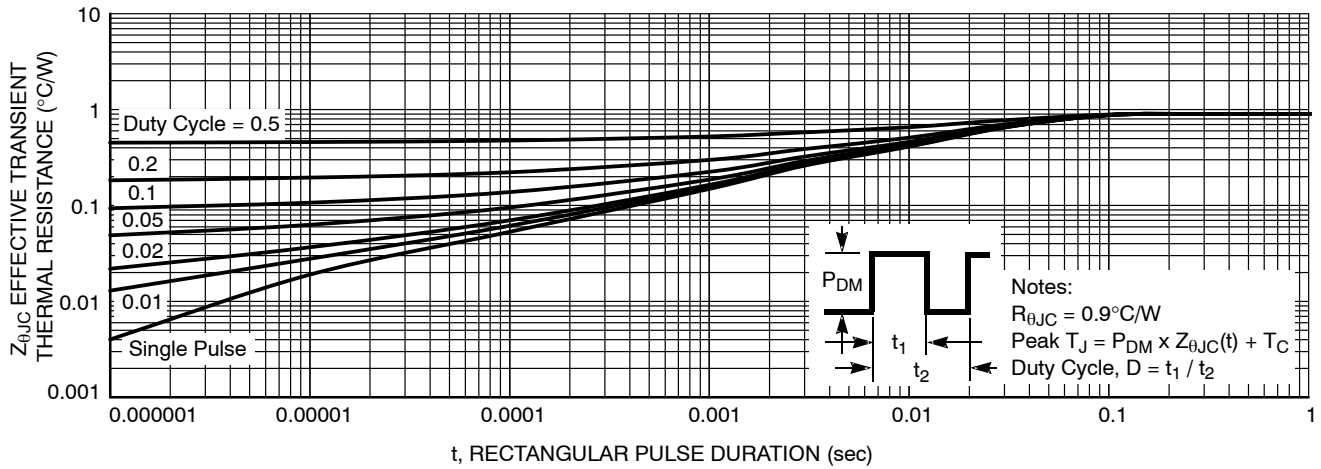


Figure 13. Transient Thermal Impedance

ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
NTMFSC1D0N04HL	1D0N04	DFN8 5x6.15 (Pb-Free/Halogen Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

